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(74) Agents: **CONNORS, Matthew, E.** et al.; Gauthier & Connors, LLP, 225 Franklin Street, Suite 3300, Boston, MA 02110 (US).

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(71) Applicant (*for all designated States except US*): **MASSACHUSETTS INSTITUTE OF TECHNOLOGY** [US/US]; 77 Massachussets Avenue, Cambridge, MA (US).

(72) Inventors; and

(75) Inventors/Applicants (*for US only*): **YI, Yasha** [CN/US]; 162 Summer Street, Apt. 22, Somerville, MA 02143 (US). **KIMERLING, Lionel, C.** [US/US]; 369 Strawberry Hill Road, Concord, MA 01742 (US). **DUAN, Xiaoman** [US/US]; 6 Estes Street, Amesbury, MA 01913 (US). **ZENG, Lirong** [CN/US]; 350 Memorial Drive, Apt. 16C2, Cambridge, MA 02139 (US).

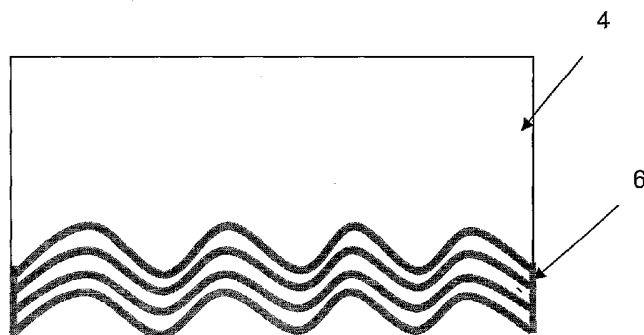
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(54) Title: LIGHT TRAPPING IN THIN FILM SOLAR CELLS USING TEXTURED PHOTONIC CRYSTAL

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(57) Abstract: A solar cell includes a photoactive region that receives light. A photonic crystal is coupled to the photoactive region, wherein the photonic crystal comprises a distributed Bragg reflector (DBR) for trapping the light.

LIGHT TRAPPING IN THIN FILM SOLAR CELLS USING TEXTURED PHOTONIC CRYSTAL

PRIORITY INFORMATION

5 This application claims priority from provisional application Ser. No. 60/645,766
filed January 19, 2005.

BACKGROUND OF THE INVENTION

10 The invention relates to the field solar cells, in particular to photonic
microstructure used in conjunction with solar cells.

Photovoltaic cells, commonly known as solar cells, are well known devices that
convert light energy into electricity. Solar cells provide a number of advantages when
compared to conventional energy sources. For example, solar cells produce electricity
without pollution and do not use the dwindling fossil fuel supply.

15 Silicon is one of the most popular materials for making solar cells. A silicon solar
cell is conventionally created by doping the silicon to form an n-type layer and p-type
layer. The n and p-type layers form a p-n junction in the silicon. When light illuminates
the solar cell, some photons are able to excite electrons from their valence band to the
conduction band and to produce electron/hole pairs. The electrons are swept into the n-
20 type layer, while the holes are swept to the p-type layer. Because of the presence of the
p-n junction, most of these electron/hole pairs cannot recombine, thereby leaving them to
produce an electric current in an external circuit. The photons that can free electrons
have a photon energy that is at least equal to and usually higher than the silicon band-gap
energy.

25 Such arrangement is very limited in essentially using the light received for direct
photovoltaic purposes.

SUMMARY OF THE INVENTION

30 According to one aspect of the invention, there is provided a solar cell. The solar
cell includes a photoactive region that receives light. A photonic crystal is coupled to the
photoactive region, wherein the photonic crystal comprises a distributed Bragg reflector
(DBR) for trapping the light.

According to another aspect of the invention, there is provided a method of

forming a solar cell. The method includes forming a photoactive region that receives light. A photonic crystal is formed that is coupled to the photoactive region, wherein the photonic crystal comprises a distributed Bragg reflector (DBR) for trapping the light.

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BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic diagram illustrating a solar cell structure that includes a photonic crystal structure;

FIG. 2 is a schematic diagram illustrating a photonic structure that is used according to the invention to trap light,

10 FIG. 3 is a table demonstrating the relation between the wavelength of the incident light, angle, and efficiency;

FIG. 4 is a schematic diagram illustrating an embodiment of the invention which utilizes distributed Bragg reflector (DBR) gratings to form the photonic structure;

15 FIG. 5 is a graph illustrating the simulation and measurement of Si/Si₃N₄ DBR reflectivity; and

FIG. 6 is a graph illustrating the light bending characteristics of the inventive DBR gratings used the inventive backside reflector

DETAILED DESCRIPTION OF THE INVENTION

20 The invention utilizes a photonic microstructure, in conjunction with thin silicon solar cells in order to enhance cell efficiency. The structure should increase the optical path length of wasted photons by creating anomalous refraction effects.

In order to improve thin film solar cell efficiency, the invention uses a light-trapping scheme that can tremendously enhance optical path length and make light
25 almost completely absorbed by using novel photonic structure on the backside reflector.

The invention utilizes a photonic structure to trap light. This arrangement would allow strong light bending so that reflected light is almost in the parallel direction of the absorption layer.

FIG. 1 illustrates a solar cell structure 2 that includes a backside reflector
30 structure 6. Solar cell 2 is preferably a thin Si solar cell. Solar cell 2 has a photoactive region 4 with a wavered backside reflector 6 formed, for example, from wavered DBR gratings. Any incident wave in the frequency range arriving onto the backside reflector 6 will be reflected almost in the parallel direction at a large angle.

The backside reflector structure 6 is an one dimensional photonic crystal that acts as a "perfect" mirror whose reflectance can be controlled to be more than 99.96%.

FIG. 2 illustrates a wavered backside reflector structure 10 that is used according to the invention to trap light. The wavered backside reflector comprises a 1D omnidirectional photonic crystal 10 formed by wavered Si-based distributed Bragg reflector (DBR) gratings 12. Photonic crystals are periodic dielectric structures that have a photonic band gap (PBG) that forbids propagation of a certain frequency range of light.

The way the wavered backside reflector 10 works is when incident light comes into contact the structure 10 the light is reflected away at an angle α . The amount of energy that is still retained after reflection is computed is an efficiency factor. The higher the efficiency factor the better the more efficient and more energy of light is retained when reflected.

FIG. 3 illustrates a table demonstrating the relation between the wavelength of the incident light, angle, and efficiency. Note there is a gradual increase in the efficiency and angle of reflection that corresponds to the incidental wavelength. But at the incidental wavelength of 1560 nm and higher, the efficiency drops and the angle of incident also decreases.

FIG. 4 illustrates the wavered distributed Bragg reflector (DBR) gratings 14 used to form the photonic structure. The DBR used in accordance with this embodiment is a Si DBR, however other DBRs can be also be used which have similar properties as the Si DBR. In FIG. 4, the DBR grating utilizes a combination of Si/Si₃N₄ pairs 16. This arrangement produces a reflectivity of 99.6%, while a Si/SiO₂ pair arrangement can produce a reflectivity of 99.98%. FIG. 5 illustrates the simulation and measurement of Si/Si₃N₄ DBR reflectivity.

The inventive back reflector design combines distributed Bragg reflector (DBR) with reflection grating. It makes incident light strongly bent and reflected almost parallel to the surface of the absorption layer, hence the optical path length can be enhanced by tens of thousands of times, more than two orders of magnitude longer than that obtained by conventional light trapping schemes.

Furthermore, it provides extremely high reflectivity with large omnidirectional bandgap over several hundred nanometers in the solar spectrum range. Therefore, incident light can be almost completely absorbed. In turn, quantum efficiency of the solar cell based on the photonic structure should be improved significantly.

To maximize the open-circuit voltage of a solar cell, it is important to minimize carrier recombination, one effective way of which is to reduce film thickness. However, one needs to maintain high light absorbing capability.

The DBR grating can be developed using a practical fabrication process for Si
5 grating DBR with current CMOS compatibility on a Si substrate. First, optical projection lithography is used to pattern substrate into gratings with period in the order of wavelength, then HBr plasma is used to accurately control etch depth. Afterwards DBR stacks are deposited using LPCVD using Si_3N_4 : DichlorSilane (SiCl_2H_2) and Ammonia (NH_3) at 200mTorr, 775°C and Poly-Si: Silane (SiH_4) at 150 – 300 mTorr,
10 625°C. Note PECVD can also be used from fabrication.

The periodicity of the gratings is in the order of wavelength so as to be in a strong diffraction regime, which is defined as $\lambda_g/n_{\text{Si}} \approx 1.1 \mu\text{m} / n_{\text{Si}}$. The depth of the grating is defined as $\lambda/4n_{\text{Si}}$ to cancel 0th order light. The cancellation of 0th order and +1 and -1 order is to achieve high angle bending.

15 FIG. 6 shows the light bending characteristics of the inventive DBR gratings used the inventive backside reflector. The graph shows light bending angle increases with wavelength. Light with $\lambda > 310 \text{ nm}$ can be total internally reflected. Light with λ between $0.8\mu\text{m}$ and $1.1\mu\text{m}$ light can be bent by 47° to 90° and form a guided mode. Optical pathlength enhancement can be as large as 10^5 times.

20 Although the present invention has been shown and described with respect to several preferred embodiments thereof, various changes, omissions and additions to the form and detail thereof, may be made therein, without departing from the spirit and scope of the invention.

What is claimed is:

CLAIMS

- 1 1. A solar cell comprising:
 - 2 a photoactive region that receives light; and
 - 3 a photonic crystal that is coupled to said photoactive region, wherein said
 - 4 photonic crystal comprises a grating distributed Bragg reflector (DBR) for trapping said
 - 5 light.
- 1 2. The solar cell of claim 1, wherein said photonic comprises a grating Si DBR.
- 1 3. The solar cell of claim 1, wherein said grating Si DBR comprises a plurality of
 - 2 Si/Si₃N₄ pairs.
- 1 4. The solar cell of claim 1, wherein said grating Si DBR comprises a plurality of
 - 2 Si/SiO₂ pairs.
- 1 5. The solar cell of claim 3, wherein said Si/Si₃N₄ pairs produce a reflectivity of 99.6%.
- 1 6. The solar cell of claim 4, wherein said Si/SiO₂ pairs produce a reflectivity of 99.98%.
- 1 7. A method of forming solar cell comprising:
 - 2 forming a photoactive region that receives light; and
 - 3 forming a photonic crystal that is coupled to said photoactive region, wherein
 - 4 said photonic crystal comprises a distributed Bragg reflector (DBR) for trapping said
 - 5 light.
- 1 8. The method of claim 7, wherein said photonic comprises a grating Si DBR.
- 1 9. The method of claim 7, wherein said grating Si DBR comprises a plurality of Si/Si₃N₄
 - 2 pairs.
- 1 10. The method of claim 7, wherein said grating Si DBR comprises a plurality of
 - 2 Si/SiO₂ pairs.
- 1 11. The method of claim 9, wherein said Si/Si₃N₄ pairs produce a reflectivity of 99.6%.
- 1 12. The method of claim 10, wherein said Si/SiO₂ pairs produce a reflectivity of
 - 2 99.98%.

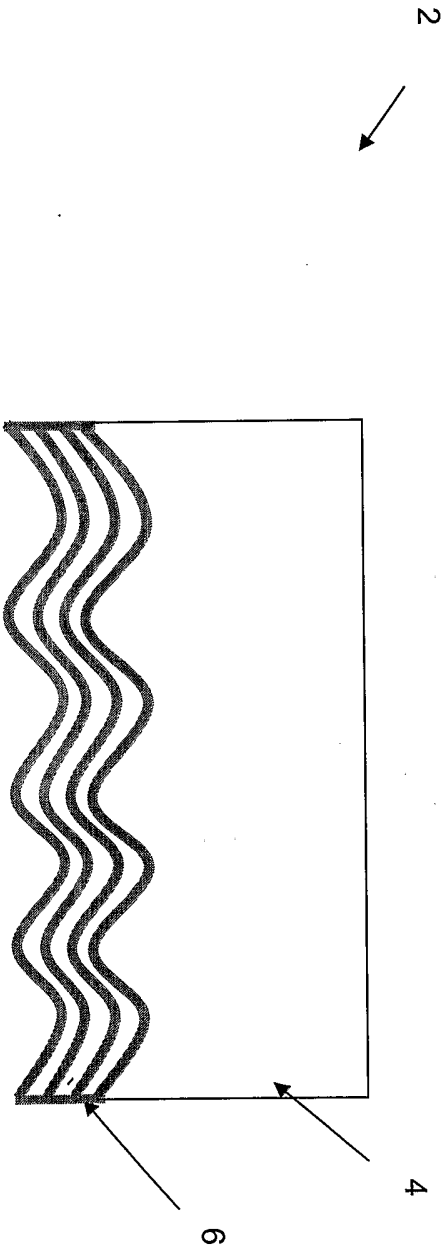


FIG. 1

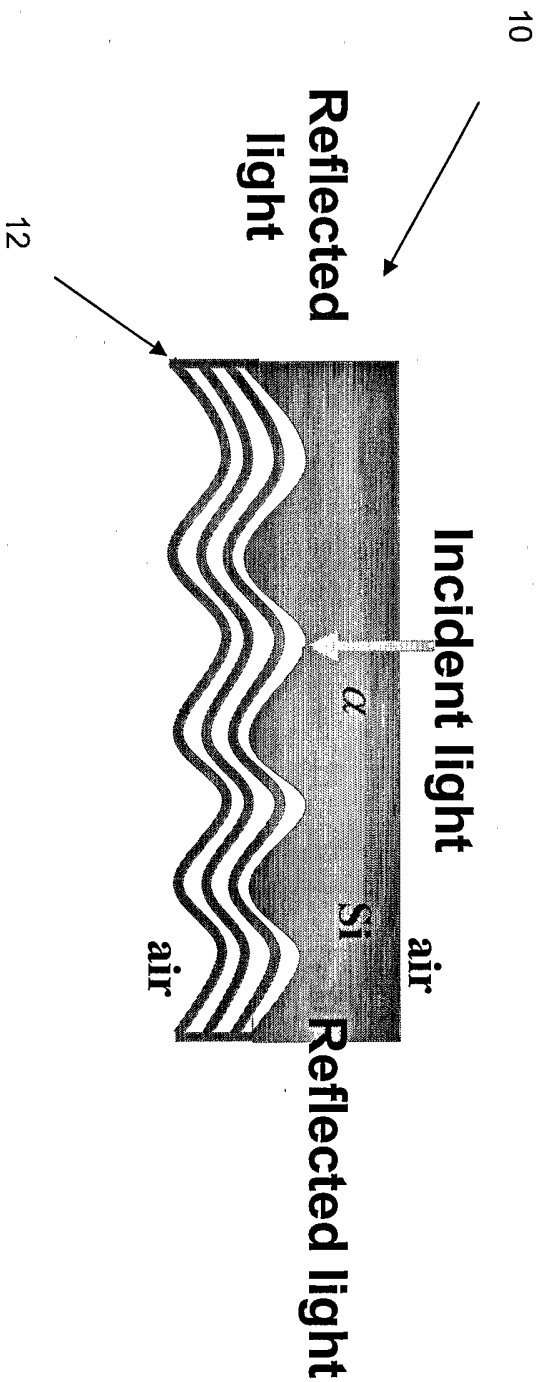


FIG. 2

Wavelength	Bending angle (α)	Efficiency
1500 nm	70°	73%
1510 nm	71.2°	76%
1520 nm	72.6°	77%
1530 nm	73.3°	77.5%
1540 nm	75°	76.4%
1550 nm	76.5°	74%
1560 nm	78.2°	70%
1570 nm	81°	64%
1580 nm	83°	53%

FIG. 3

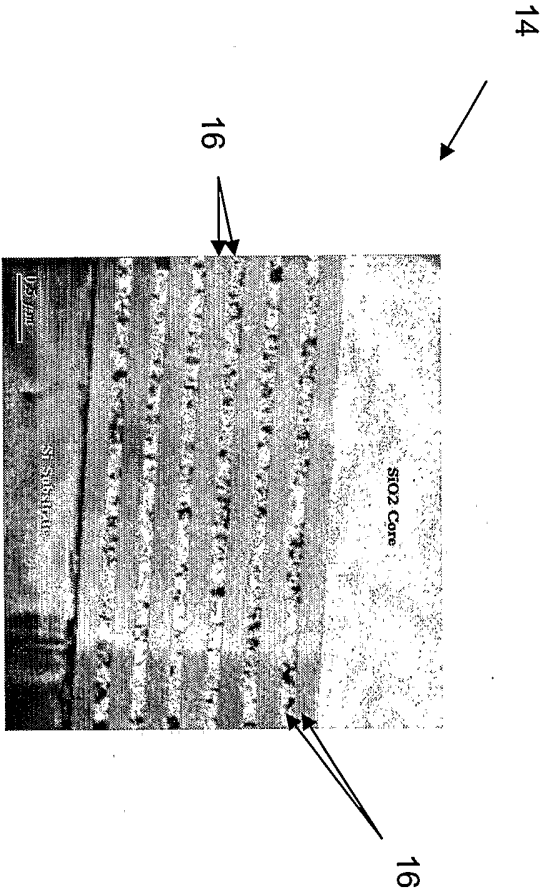


FIG. 4

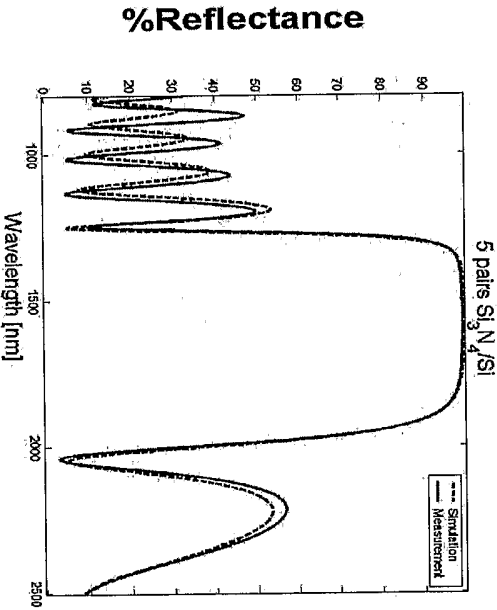


FIG. 5

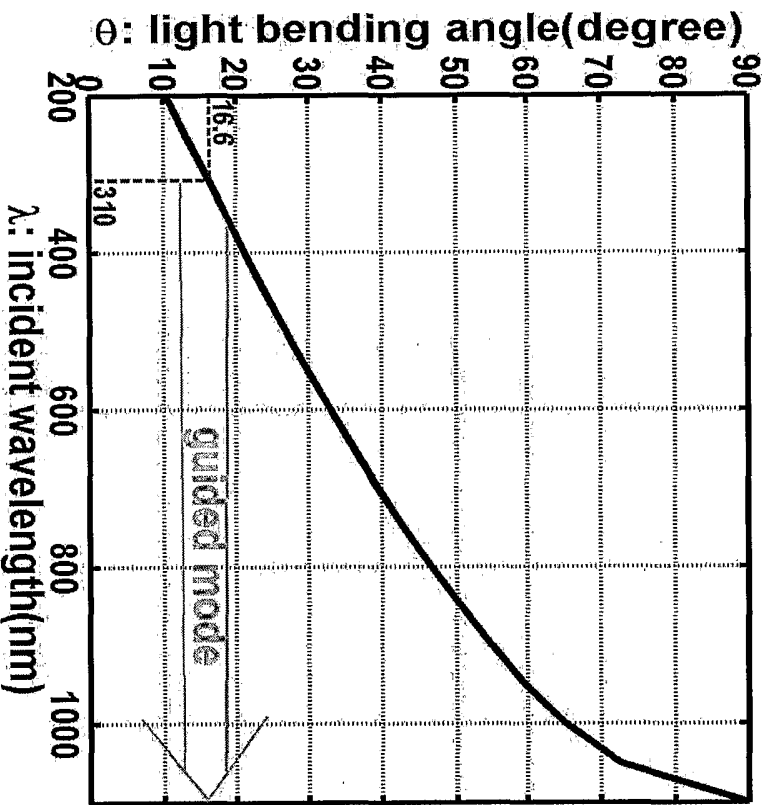


FIG. 6

INTERNATIONAL SEARCH REPORT

International Application No
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A. CLASSIFICATION OF SUBJECT MATTER

H01L31/052

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data, PAJ, INSPEC, IBM-TDB

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	WO 03/001609 A (MASSACHUSETTS INSTITUTE OF TECHNOLOGY) 3 January 2003 (2003-01-03) page 3, lines 2-20	1-12
X	MAUK M G ET AL: "Buried metal/dielectric/semiconductor reflectors for light trapping in epitaxial thin-film solar cells" IEEE - CONFERENCE PROCEEDINGS ARTICLE, 13 May 1996 (1996-05-13), pages 147-150, XP010208114 page 149, right-hand column, paragraph 2	1-12

☒ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

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- *O* document referring to an oral disclosure, use, exhibition or other means
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European Patent Office, P.B. 5818 Patentlaan 2
NL - 2280 HV Rijswijk
Tel. (+31-70) 340-2040, Tx. 31 651 epo nl,
Fax: (+31-70) 340-3016

Authorized officer

Ekoué, A

INTERNATIONAL SEARCH REPORT

International Application No
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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	HIROSHI WADA ET AL: "EFFECTS OF NONUNIFORM CURRENT INJECTION IN GAINASP/INP VERTICAL-CAVITY LASERS" APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE OF PHYSICS, MELVILLE, NY, US, vol. 60, no. 24, 15 June 1992 (1992-06-15), pages 2974-2976, XP000269914 ISSN: 0003-6951 figure 1 -----	1-12

INTERNATIONAL SEARCH REPORT

Information on patent family members

International Application No

.../US2005/027264

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
WO 03001609	A	03-01-2003	NONE